

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 136 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	-	4	A
Tj	junction temperature		-	-	175	°C
Static charact	eristics					
V _F	forward voltage	I _F = 4 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V





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NXPSC04650

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic chara	acteristics					
Qr	recovered charge	$I_F = 4 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \underline{Fig. 5}$	-	7	-	nC

5. Pinning information

Symbol K A	Description cathode	Simplified outline	Graphic symbol
	cathode	mb	
А			K A
	anode	205	001aaa020
mb	mounting base; connected to cathode	TO-220AC (SOD59A)	
1	пb	_	cathode

6. Ordering information

Table 3.	Ordering information	

Type number	Package					
	Name	Description	Version			
NXPSC04650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A			

7. Marking

Table 4. Marking codes	
Type number	Marking code
NXPSC04650	NXPSC04650

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	650	V
V _{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 136 °C; square-wave pulse; <u>Fig. 1</u> ; Fig. 2	-	4	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 µs; T _{mb} ≤ 136 °C; square-wave pulse	-	8	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	24	A
		t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	-	235	A
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

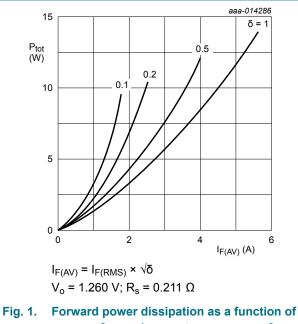


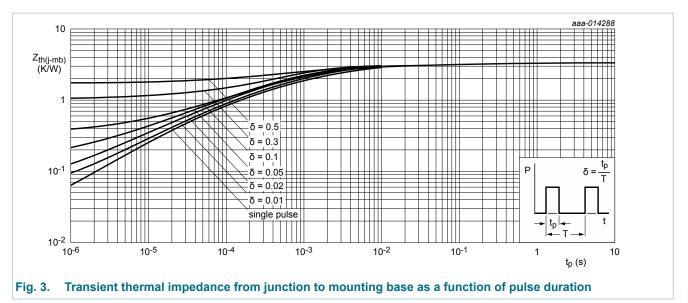


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

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9. Thermal characteristics

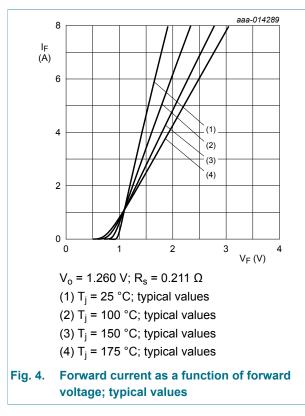
Table 6. T	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	3.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

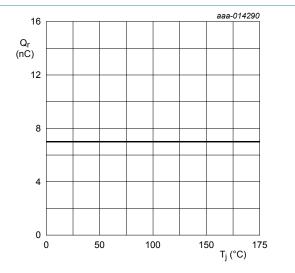


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10. Characteristics

Table 7. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	octeristics					
V _F	forward voltage	I _F = 4 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V
		I _F = 4 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.8	2.1	V
I _R reverse current		V _R = 650 V; T _j = 25 °C	-	-	170	μA
		V _R = 650 V; T _j = 150 °C	-	-	550	μA
Dynamic ch	aracteristics					
Qr	recovered charge	$I_{F} = 4 \text{ A; } dI_{F}/dt = 500 \text{ A}/\mu\text{s; } V_{R} = 400 \text{ V;}$ $T_{j} = 25 \text{ °C; } \frac{\text{Fig. 5}}{5}$	-	7	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	130	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	16	-	pF
		f = 1 MHz; V_R = 600 V; T_j = 25 °C	-	13	-	pF



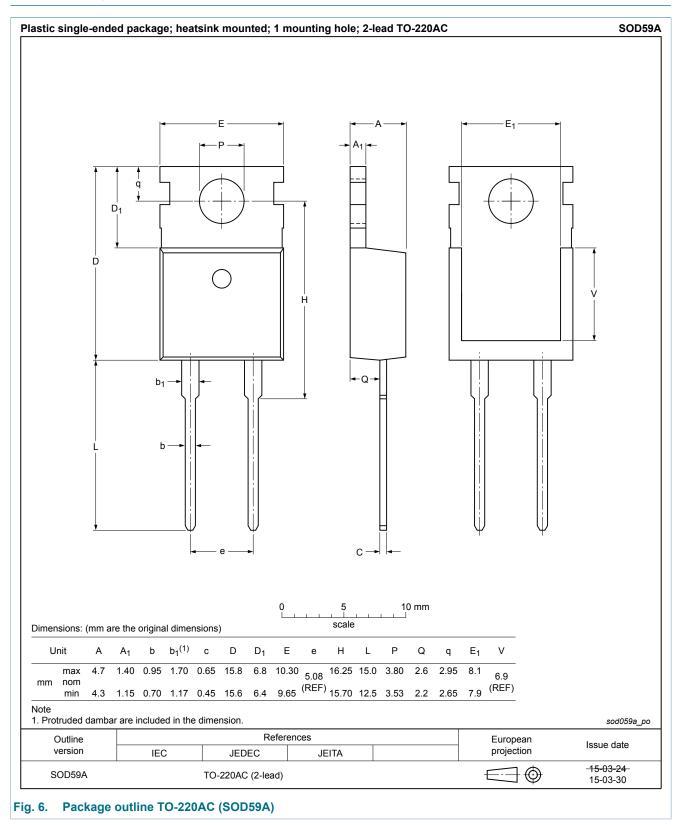






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11. Package outline



NXPSC04650

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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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